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- (71) **Applicant:** **NEWSOUTH INNOVATIONS PTY LTD**
[AU/AU]; Rupert Myers Building Gate 14, Barker Street
UNSW, Sydney, New South Wales 2052 (AU).
- (72) **Inventors:** **WESTERN, Ned**; c/- NewSouth Innovations
Pty Limited, Rupert Myers Building, Gate 14, Barker
Street, UNSW, Sydney, New South Wales 2052 (AU).
BREMNER, Stephen; C/-Newsouth Innovations Pty Ltd,

Rupert Myers Building, Gate 14, Barker Street UNSW,
Sydney, New South Wales 2052 (AU).

- (74) **Agent:** **GRIFFITH HACK**; Level 19, 109 St. George Ter-
race, Perth, Western Australia 6000 (AU).

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- (54) **Title:** A METHOD OF FORMING A CONTACT FOR A PHOTOVOLTAIC CELL

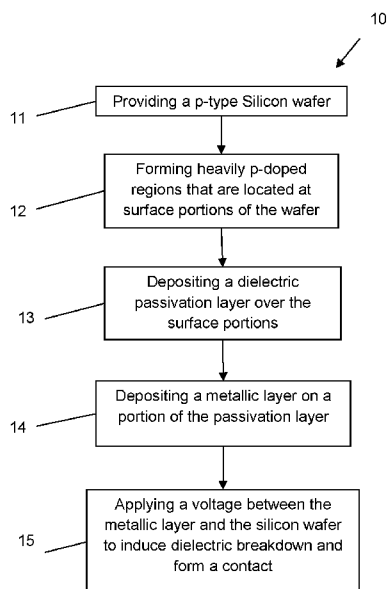


Figure 1

- (57) **Abstract:** The present disclosure provides a method of forming a con-
tact for a photovoltaic (PV) cell. The method comprises the step of providing
a substrate of a semiconductor material. The substrate has first regions that
have a first doping property and are located at first surface portions. The
method also comprises depositing a passivation layer on the surface of the
substrate including the first surface portions. Further, the method comprises
depositing a conductive layer on the passivation layer such that material of
the passivation layer is sandwiched between the first regions and the con-
ductive layer. In addition, the method comprises applying an electric field
between the first regions and the conductive layer in a manner such that loc-
ally a dielectric breakdown of the sandwiched passivation layer material is in-
duced. The first regions have a doping property and the method is conducted
such that an electrical resistance is reduced in the passivation layer at the first
regions and an electrical contact is formed.



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